Ilya A Eliseyev

List of Publications by Year
in descending order

48	299	933264	996849
papers	citations	10 h-index	15 g-index

48	48	48	284
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Photoluminescence enhancement in multilayered MoSe₂ nanostructures obtained by local anodic oxidation. 2D Materials, 2022, 9, 015010.	2.0	2
2	A Blueprint for the Synthesis and Characterization of Thiolated Graphene. Nanomaterials, 2022, 12, 45.	1.9	3
3	MoS₂ flake as a van der Waals homostructure: luminescence properties and optical anisotropy. Nanoscale, 2021, 13, 17566-17575.	2.8	7
4	Phonons in Short-Period GaN/AlN Superlattices: Group-Theoretical Analysis, Ab initio Calculations, and Raman Spectra. Nanomaterials, 2021, 11, 286.	1.9	14
5	Graphene on SiC Substrate as Biosensor: Theoretical Background, Preparation, and Characterization. Materials, 2021, 14, 590.	1.3	15
6	Modification of the Electronic Structure of Quasi-Free-Standing Graphene by the Adsorption and Intercalation of Mn Atoms. Journal of Experimental and Theoretical Physics, 2021, 132, 906-916.	0.2	3
7	Photoluminescence Kinetics of Dark and Bright Excitons in Atomically Thin MoS₂. Physica Status Solidi - Rapid Research Letters, 2021, 15, 2100263.	1.2	4
8	The Effect of Interface Diffusion on Raman Spectra of Wurtzite Short-Period GaN/AlN Superlattices. Nanomaterials, 2021, 11, 2396.	1.9	5
9	Quasi-freestanding graphene on SiC(0001) via cobalt intercalation of zero-layer graphene. Physical Review B, 2021, 104, .	1.1	8
10	Surface Nanostructuring during Selective Area Epitaxy of Heterostructures with InGaAs QWs in the Ultra-Wide Windows. Nanomaterials, 2021, 11, 11.	1.9	11
11	Investigation of electrolysis-related modification of graphene films in biosensors. Journal of Physics: Conference Series, 2021, 2103, 012103.	0.3	0
12	Analysis of the sharpness of interfaces in short-period GaN/AlN superlattices using Raman spectroscopy data. Journal of Physics: Conference Series, 2021, 2103, 012147.	0.3	1
13	Surface morphology control of the SiC (0001) substrate during the graphene growth. Fullerenes Nanotubes and Carbon Nanostructures, 2020, 28, 281-285.	1.0	5
14	Investigation of epitaxial graphene via Raman spectroscopy: Origins of phonon mode asymmetries and line width deviations. Carbon, 2020, 170, 666-676.	5.4	12
15	Structural and Dynamical Properties of Short-Period GaN/AlN Superlattices: Experiment and Theory. Semiconductors, 2020, 54, 1706-1709.	0.2	0
16	A Study of the Photoresponse in Graphene Produced by Chemical Vapor Deposition. Semiconductors, 2020, 54, 991-998.	0.2	0
17	Temperature activation of indirect exciton in nanostructures based on MoS₂. Journal of Physics: Conference Series, 2020, 1482, 012038.	0.3	6
18	Detection of lysine molecular ions in solution gated field effect transistors based on unmodified graphene. Journal of Applied Physics, 2020, 128, 215302.	1.1	2

#	Article	IF	Citations
19	Local anodic oxidation as a method of fabrication optoelectronic devices based on thin TMDC layers. AIP Conference Proceedings, 2020, , .	0.3	1
20	State-of-the-art and prospects for intense red radiation from coreâ€“shell InGaN/GaN nanorods. Scientific Reports, 2020, 10, 19048.	1.6	10
21	Transformation of the buffer layer grown on 4H-SiC to single-layer graphene by ex situ hydrogen intercalation. Fullerenes Nanotubes and Carbon Nanostructures, 2020, 28, 316-320.	1.0	1
22	Comparison of graphene films grown on 6H-SiC and 4H-SiC substrates. Fullerenes Nanotubes and Carbon Nanostructures, 2020, 28, 321-324.	1.0	2
23	Raman and AFM studies of epitaxial graphene intended for manufacturing of transistors. Journal of Physics: Conference Series, 2020, 1695, 012018.	0.3	1
24	Raman scattering and low-frequency noise in epitaxial graphene chips. Journal of Physics: Conference Series, 2020, 1697, 012130.	0.3	3
25	Raman Studies of Graphene Films Grown on 4H-SiC Subjected to Deposition of Ni. Semiconductors, 2020, 54, 1674-1677.	0.2	0
26	Comparative Study of Conventional and Quasi-Freestanding Epitaxial Graphenes Grown on 4H-SiC Substrate. Semiconductors, 2020, 54, 1657-1660.	0.2	0
27	Localization and transient emission properties in InGaN/GaN quantum wells of different polarities within coreâ€“shell nanorods. Nanoscale, 2019, 11, 193-199.	2.8	10
28	Radiation Defects in Heterostructures 3C-SiC/4H-SiC. Crystals, 2019, 9, 115.	1.0	10
29	Phonons in short-period (GaN)_m(AlN)_n superlattices: ab initio calculations and group-theoretical analysis of modes and their genesis. Journal of Physics: Conference Series, 2019, 1400, 066016.	0.3	3
30	Raman spectra of interface phonons in long-period AlN/GaN superlattices as a tool for determination of the structure period. Journal of Physics: Conference Series, 2019, 1400, 066003.	0.3	1
31	Investigation of the Hydrogen Etching Effect of the SiC Surface on the Formation of Graphene Films. Technical Physics, 2019, 64, 1843-1849.	0.2	3
32	Boson Peak Related to Ga Nanoclusters in AlGaN Layers Grown by Plasma-Assisted Molecular Beam Epitaxy at Ga-Rich Conditions. Semiconductors, 2019, 53, 1479-1488.	0.2	1
33	Optical Estimation of the Carrier Concentration and the Value of Strain in Monolayer Graphene Grown on 4H-SiC. Semiconductors, 2019, 53, 1904-1909.	0.2	9
34	Raman spectra of GaSe epitaxial layers grown on GaAs substrates and group-theoretical analysis of their vibrational modes. Journal of Physics: Conference Series, 2019, 1400, 055007.	0.3	0
35	Raman spectroscopy estimation of the carrier concentration and the value of strain in monolayer graphene films grown on 4H-SiC. Journal of Physics: Conference Series, 2019, 1400, 055037.	0.3	1
36	State memory in solution gated epitaxial graphene. Applied Surface Science, 2018, 444, 36-41.	3.1	4

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37	Study of properties and development of sensors based on graphene films grown on SiC (0001) by thermal destruction method. Journal of Physics: Conference Series, 2018, 951, 012007.	0.3	6
38	High Quality Graphene Grown by Sublimation on 4H-SiC (0001). Semiconductors, 2018, 52, 1882-1885.	0.2	9
39	Multiwall MoS2 tubes as optical resonators. Applied Physics Letters, 2018, 113, .	1.5	30
40	Growth of III-N/graphene heterostructures in single vapor phase epitaxial process. Journal of Crystal Growth, 2018, 504, 1-6.	0.7	14
41	Intercalation of Iron Atoms under Graphene Formed on Silicon Carbide. Physics of the Solid State, 2018, 60, 1439-1446.	0.2	11
42	Graphene on silicon carbide as a basis for gas- and biosensor applications. Nanosystems: Physics, Chemistry, Mathematics, 2018, , 95-97.	0.2	3
43	Comparative characterization of graphene grown by chemical vapor deposition, transferred to nonconductive substrate, and subjected to Ar ion bombardment using X-ray photoelectron and Raman spectroscopies. Diamond and Related Materials, 2017, 76, 14-20.	1.8	12
44	Transport properties of graphene films grown by thermodestruction of SiC (0001) surface in argon medium. Technical Physics Letters, 2017, 43, 849-852.	0.2	3
45	Study of the crystal and electronic structure of graphene films grown on 6H-SiC (0001). Semiconductors, 2017, 51, 1072-1080.	0.2	44
46	Complex XPS and Raman Study of Graphene on Copper and Si/SiO₂ Subjected to Ar Ion Treatment. Key Engineering Materials, 0, 721, 258-262.	0.4	6
47	Comparative Investigation of the Graphene-on-Silicon Carbide and CVD Graphene as a Basis for Biosensor Application. Key Engineering Materials, 0, 799, 185-190.	0.4	3
48	Graphene Quality Assessment Using an Entropy Approach of SEM Images. Materials Science Forum, 0, 1004, 525-530.	0.3	0